

N-Channel Super Junction Power MOSFET III

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

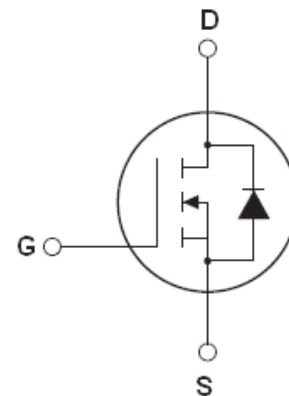
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

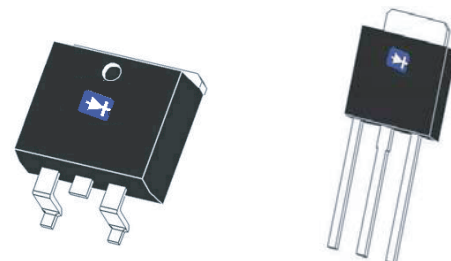
Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

V_{DS}	800	V
$R_{DS(ON)MAX}$	900	m Ω
I_D	6	A



Schematic diagram



TO-252

TO-251

Package Marking And Ordering Information

Device	Device Package	Marking
RM6N800LD	TO-252	6N800
RM6N800IP	TO-251	6N800

Table 1. Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	800	V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1$ Hz)	V_{GS}	± 30	V
Continuous Drain Current at $T_C = 25^\circ\text{C}$	$I_{D(DC)}$	6	A
Continuous Drain Current at $T_C=100^\circ\text{C}$	$I_{D(DC)}$	3.8	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	24	A
Maximum Power Dissipation($T_C = 25^\circ\text{C}$)	P_D	98	W
Derate above 25°C		0.78	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note2)	E_{AS}	100	mJ
Avalanche current (Note 1)	I_{AR}	5	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.3	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, $V_{DS} \leq 480 V$,	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480 V, I_{SD} < I_D$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	1.27	°C/W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	800			V
Zero Gate Voltage Drain Current($T_C=25^\circ C$)	I_{DSS}	$V_{DS}=800V, V_{GS}=0V$			1	μA
Zero Gate Voltage Drain Current($T_C=125^\circ C$)	I_{DSS}	$V_{DS}=800V, V_{GS}=0V$			100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3	3.5	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=4A$		780	900	m Ω
Dynamic Characteristics						
Forward Transconductance	g_{FS}	$V_{DS} = 20V, I_D = 4A$		6		S
Input Capacitance	C_{ISS}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$		1290		pF
Output Capacitance	C_{OSS}			55		pF
Reverse Transfer Capacitance	C_{RSS}			3		pF
Total Gate Charge	Q_g	$V_{DS}=640V, I_D=6A,$ $V_{GS}=10V$		24		nC
Gate-Source Charge	Q_{gs}			8.5		nC
Gate-Drain Charge	Q_{gd}			7.5		nC
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=400V, I_D=3A,$ $R_G=3\Omega, V_{GS}=10V$		10		nS
Turn-on Rise Time	t_r			5		nS
Turn-Off Delay Time	$t_{d(off)}$			53	70	nS
Turn-Off Fall Time	t_f			6	9	nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	$T_C=25^\circ C$			6	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				24	A
Forward on voltage	V_{SD}	$T_J=25^\circ C, I_{SD}=6A, V_{GS}=0V$		0.9	1.2	V
Reverse Recovery Time	t_{rr}	$T_J=25^\circ C, I_F=3A,$ $di/dt=100A/\mu s$		260		nS
Reverse Recovery Charge	Q_{rr}			1.7		μC
Peak Reverse Recovery Current	I_{rrm}			13		A

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

RATING AND CHARACTERISTICS CURVES (RM6N800IP/LD)

Figure1. Safe operating area

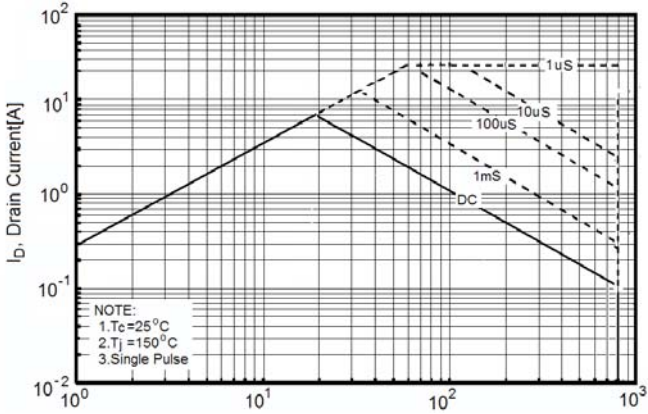


Figure2. Transient Thermal Impedance

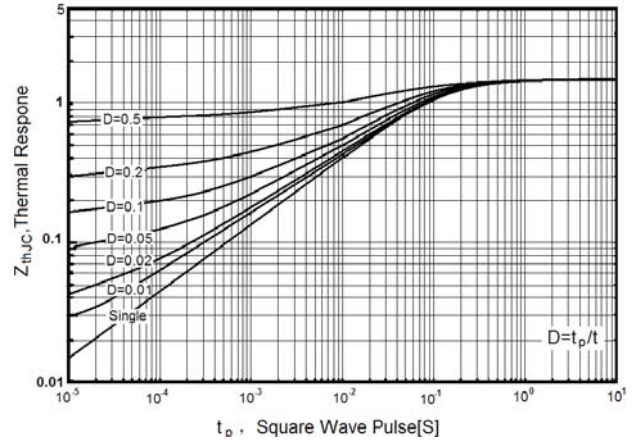


Figure3. Source-Drain Diode Forward Voltage

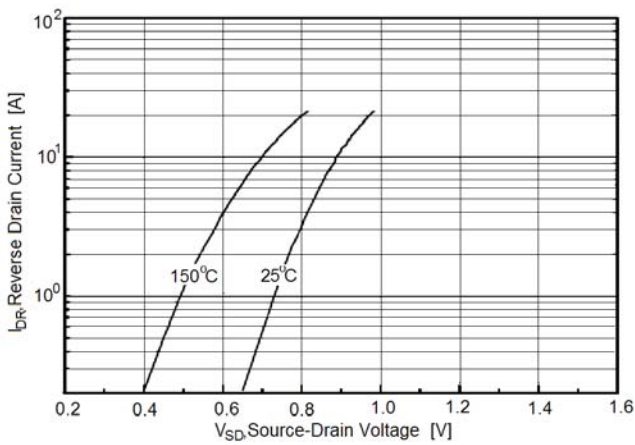


Figure4. Output characteristics

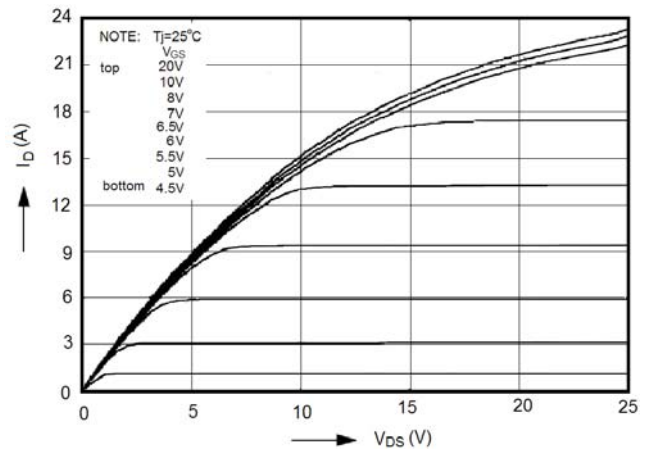


Figure5. Transfer characteristics

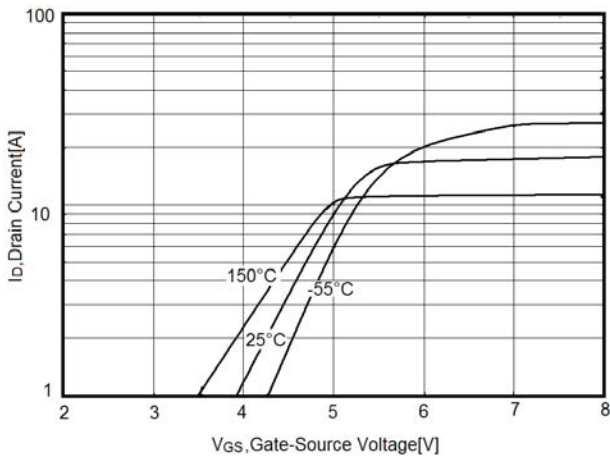
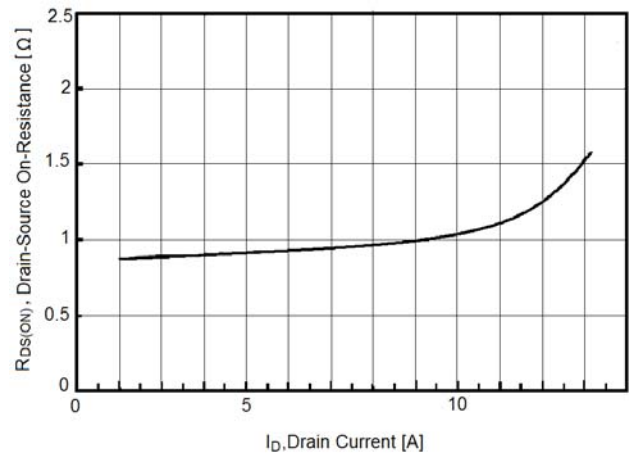


Figure6. Static drain-source on resistance



RATING AND CHARACTERISTICS CURVES (RM6N800IP/LD)

Figure7. $R_{DS(ON)}$ vs Junction Temperature

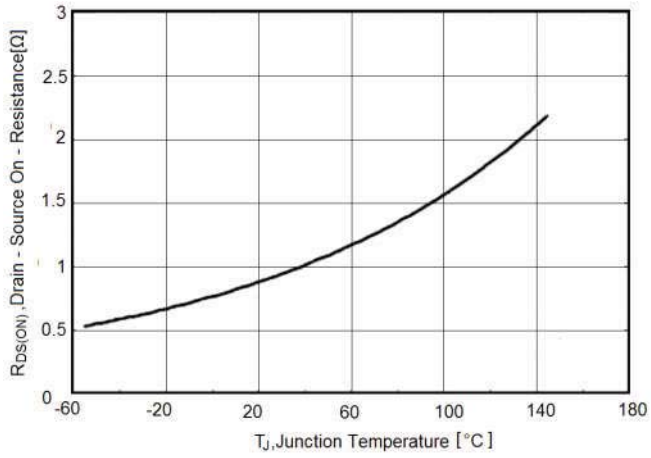


Figure8. BV_{DSS} vs Junction Temperature

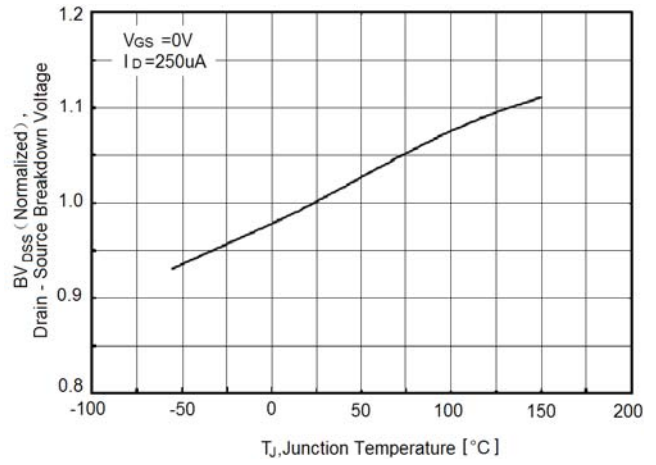


Figure9. Maximum I_D vs Junction Temperature

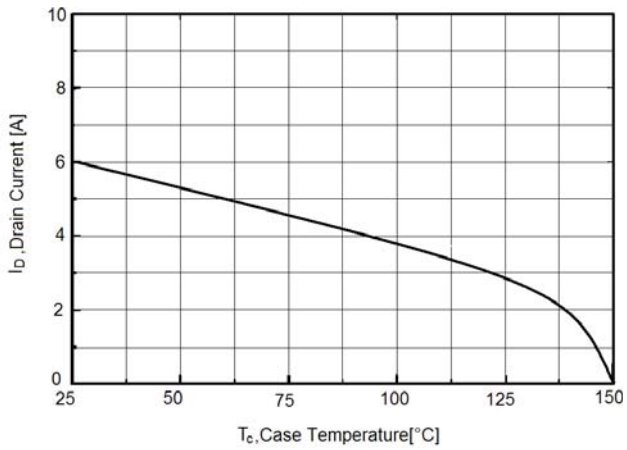
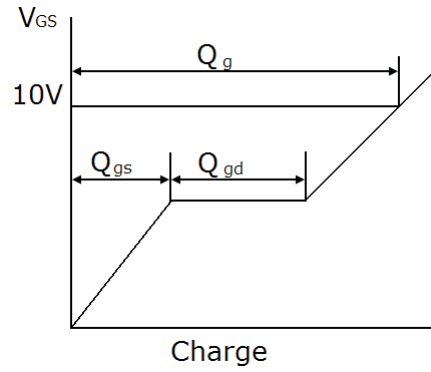
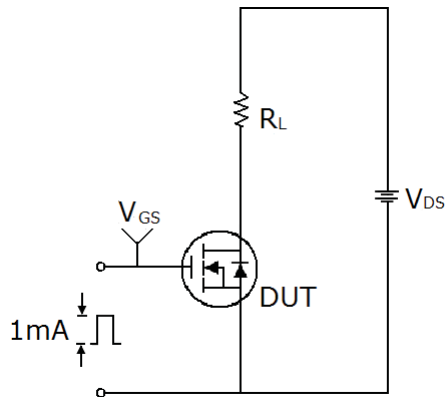


Figure10. Gate charge waveforms

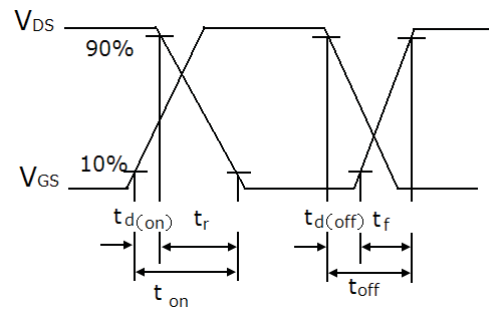
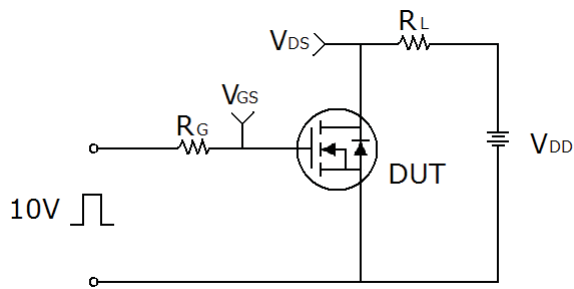
Figure11. Capacitance

Test circuit

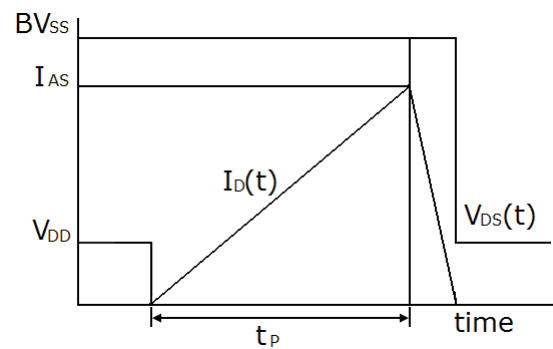
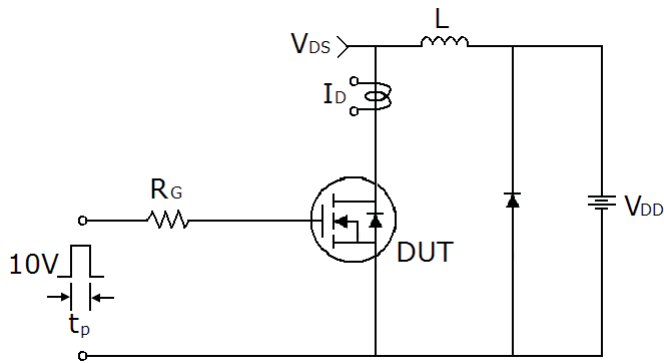
1) Gate charge test circuit & Waveform



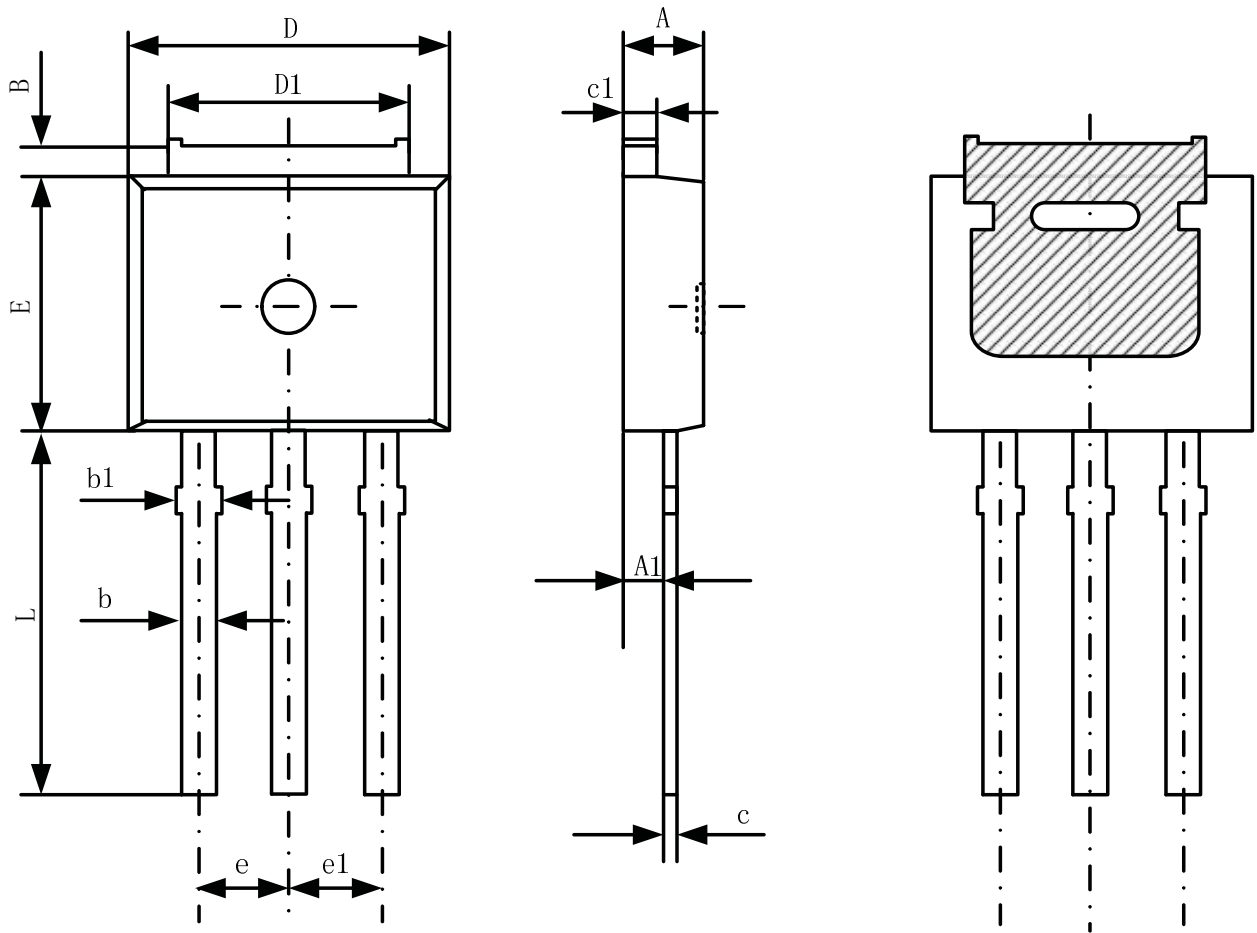
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

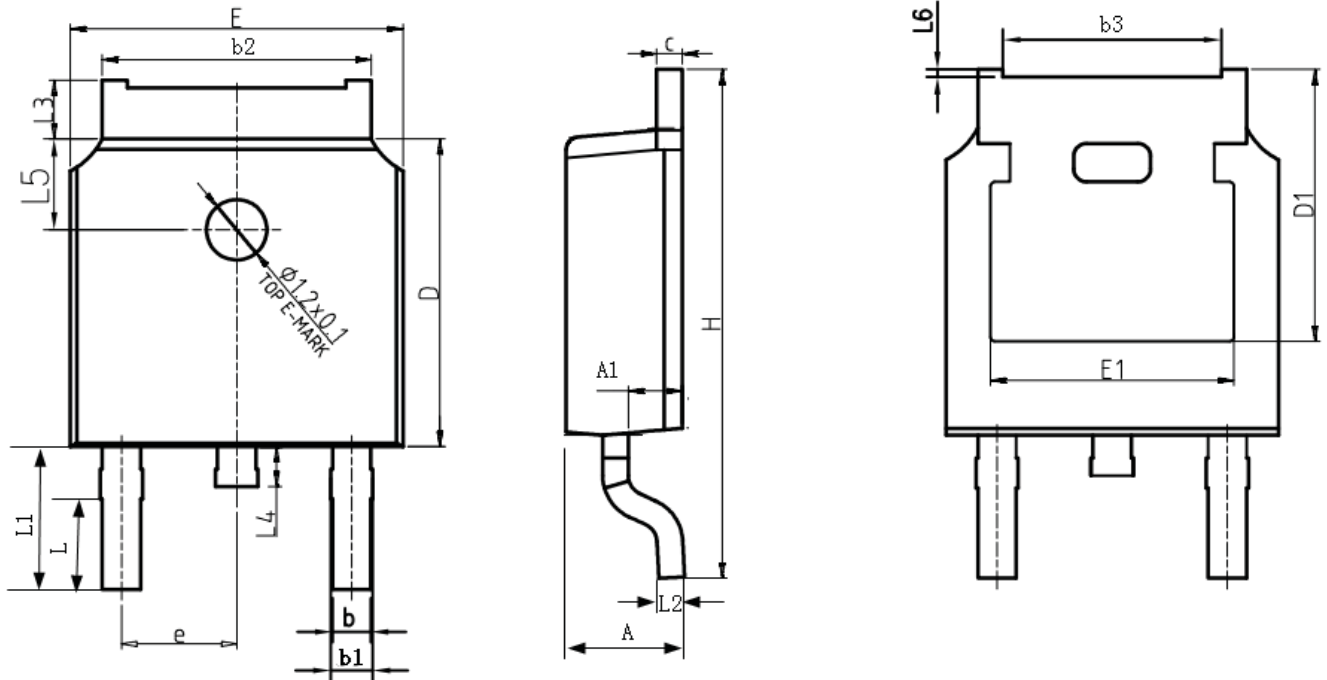


TO-251 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.100	2.500	0.083	0.099
A1	0.850	1.150	0.034	0.045
B	0.718	1.018	0.028	0.040
b	0.700	0.900	0.028	0.036
b1	0.700	1.000	0.028	0.040
c	0.408	0.608	0.016	0.024
c1	0.408	0.508	0.016	0.020
D	6.400	6.800	0.253	0.269
D1	5.180	5.480	0.205	0.217
E	5.950	6.350	0.235	0.251
e	2.286		0.090	
e1	2.286		0.090	
L	6.700	7.300	0.265	0.289

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.056	0.061
A1	0.970	1.17	0.025	0.030
b	0.720	0.850	0.018	0.022
b1	0.720	0.930	0.018	0.024
b2	5.230	5.460	0.133	0.139
b3	4.270	4.370	0.108	0.111
c	0.470	0.580	0.012	0.015
D	6.000	6.200	0.152	0.157
D1	5.300 TYP.		0.135	
E	6.500	6.700	0.165	0.170
E1	4.700	4.920	0.119	0.125
e	2.286 TYP		0.058	
L	1.400	1.700	0.036	0.043
L1	2.900 TYP.		0.074	
L2	0.510 TYP.		0.013	
L3	0.900	1.250	0.023	0.032
L4	0.600	1.000	0.015	0.025
L5	1.700	1.900	0.043	0.048
L6	0	0.1223	0.000	0.003